

Characteristic Values		Symbol	Test Conditions
\leq	5 mA	I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$
\leq	1.64 V	V_T	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$
	0.85 V 11 m Ω	V_{T0} r_T	For power-loss calculations only
\leq	1.5 V	V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$
\leq	1.6 V		$T_{VJ} = -40^\circ\text{C}$
\leq	100 mA	I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$
\leq	200 mA		$T_{VJ} = -40^\circ\text{C}$
\leq	0.2 V	V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$
\leq	5 mA	I_{GD}	
\leq	450 mA	I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$
\leq	200 mA	I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$
\leq	2 μs	t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$
0 A/ μs typ.	250 μs	t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}; t_p = 200 \mu\text{s}; di/dt = -1$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$
	0.9 KW	R_{thJC}	per thyristor / Diode; DC per module
	0.15 KW	R_{thJH}	per thyristor / Diode; DC per module
	1.1 KW		
	0.157 KW		
	16.1 mm	d_s	Creeping distance on surface
	7.5 mm	d_A	Creepage distance in air
	50 m/e ²	a	Max. allowable acceleration